METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

A technique includes forming a film on a substrate by performing a cycle a predetermined number of times, the cycle including: forming a layer on the substrate by performing a process, which includes: (a) supplying a precursor gas containing a halogen element to the substrate; and (b) supplying a reaction gas to the substrate, wherein the cycle is performed under a formation condition set based on a predetermined relationship between an amount of the halogen element contained in the layer and a proportion of crystallites oriented in a predetermined crystal plane in the film.

Fig. 3